

# SKKT 57, SKKH 57, SKKT 57B



**SEMIPACK® 1**

## Thyristor / Diode Modules

**SKKT 57**  
**SKKH 57**  
**SKKT 57B**

### Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532

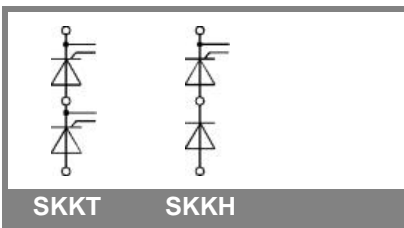
### Typical Applications

- DC motor control (e. g. for machine tools)
- AC motor soft starters
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instructions

$V_{RSM}$ V	$V_{RRM}, V_{DRM}$ V	$I_{TRMS} = 95$ A (maximum value for continuous operation) $I_{TAV} = 55$ A (sin. 180; $T_c = 80$ °C)		
900	800	SKKT 57/08E	SKKT 57B08E	SKKH 57/08E
1300	1200	SKKT 57/12E	SKKT 57B12E	SKKH 57/12E
1500	1400	SKKT 57/14E	SKKT 57B14E	SKKH 57/14E
1700	1600	SKKT 57/16E	SKKT 57B16E	SKKH 57/16E
1900	1800	SKKT 57/18E	SKKT 57B18E	SKKH 57/18E
2100	2000	SKKT 57/20EH4		SKKH 57/20EH4
2300	2200	SKKT 57/22EH4		SKKH 57/22EH4

Symbol	Conditions	Values	Units
$I_{TAV}$	sin. 180; $T_c = 85$ (100) °C;	50 (35)	A
$I_D$	P3/180; $T_a = 45$ °C; B2 / B6	57 / 68	A
	P3/180F; $T_a = 35$ °C; B2 / B6	100 / 130	A
$I_{RMS}$	P3/180F; $T_a = 35$ °C; W1 / W3	130 / 3 x 100	A
$I_{TSM}$	$T_{vj} = 25$ °C; 10 ms	1500	A
	$T_{vj} = 125$ °C; 10 ms	1250	A
$i^2t$	$T_{vj} = 25$ °C; 8,3 ... 10 ms	11000	A <sup>2</sup> s
	$T_{vj} = 125$ °C; 8,3 ... 10 ms	8000	A <sup>2</sup> s
$V_T$	$T_{vj} = 25$ °C; $I_T = 200$ A	max. 1,65	V
$V_{T(TO)}$	$T_{vj} = 125$ °C	max. 0,9	V
$r_T$	$T_{vj} = 125$ °C	max. 3,5	mΩ
$I_{DD}, I_{RD}$	for SKK .../20E, SKK .../22E	30	mA
$I_{DD}, I_{RD}$	$T_{vj} = 25$ °C; $V_{RD} = V_{RRM}, V_{DD} = V_{DRM}$	max. 15	mA
$t_{gd}$	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs	1	μs
$t_{gr}$	$V_D = 0,67 * V_{DRM}$	2	μs
$(di/dt)_{cr}$	$T_{vj} = 125$ °C	max. 150	A/μs
$(dv/dt)_{cr}$	$T_{vj} = 125$ °C	max. 1000	V/μs
$t_q$	$T_{vj} = 125$ °C	80	μs
$I_H$	$T_{vj} = 25$ °C; typ. / max.	150 / 250	mA
$I_L$	$T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max.	300 / 600	mA
$V_{GT}$	$T_{vj} = 25$ °C; d.c.	min. 3	V
$I_{GT}$	$T_{vj} = 25$ °C; d.c.	min. 150	mA
$V_{GD}$	$T_{vj} = 125$ °C; d.c.	max. 0,25	V
$I_{GD}$	$T_{vj} = 125$ °C; d.c.	max. 6	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,57 / 0,29	K/W
	sin. 180; per thyristor / per module	0,6 / 0,3	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,64 / 0,32	K/W
$R_{th(c-s)}$	per thyristor / per module	0,2 / 0,1	K/W
$T_{vj}$		- 40 ... + 125	°C
$T_{stg}$		- 40 ... + 125	°C
$V_{isol}$	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
$V_{isol}$	a. c. 50 Hz; r.m.s.; 1 s / 1 min. for SKK...H4	4800 / 4000	V~
$M_s$	to heatsink	5 ± 15 % <sup>1)</sup>	Nm
$M_t$	to terminals	3 ± 15 %	Nm
$a$		5 * 9,81	m/s <sup>2</sup>
$m$	approx.	95	g
Case	SKKT	A 46	
	SKKT ...B	A 48	
	SKKH	A 47	



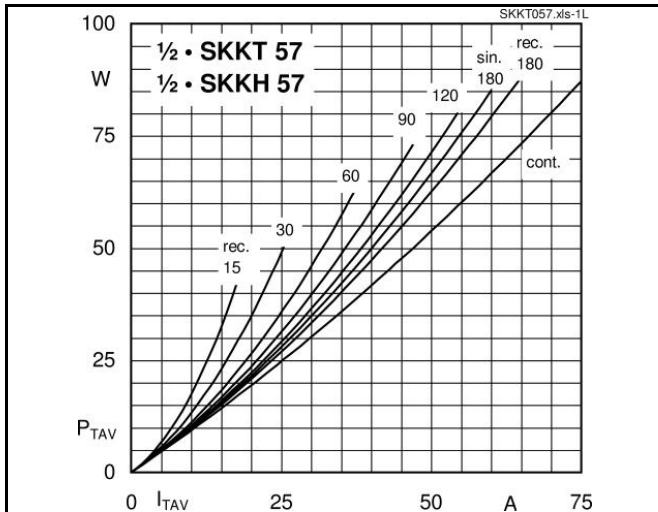


Fig. 1L Power dissipation per thyristor vs. on-state current

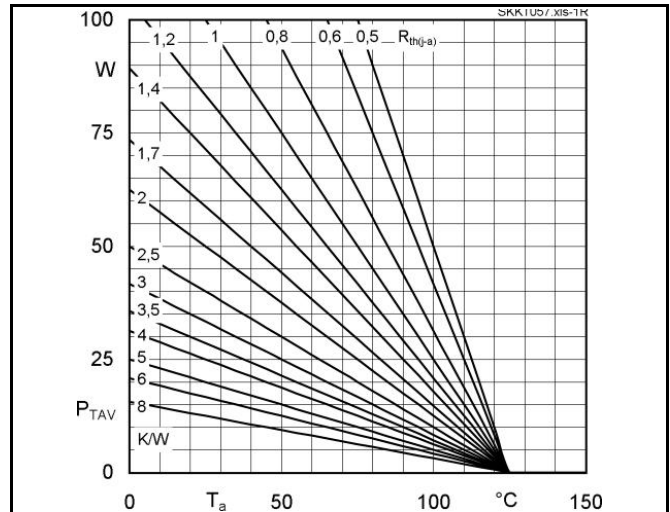


Fig. 1R Power dissipation per thyristor vs. ambient temp.

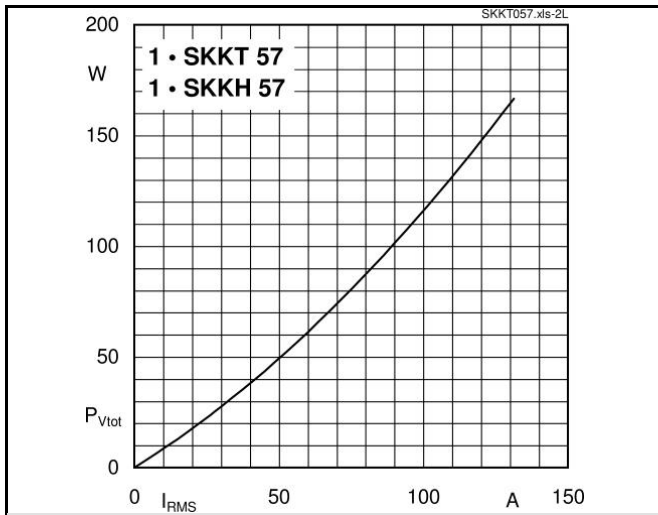


Fig. 2L Power dissipation per module vs. rms current

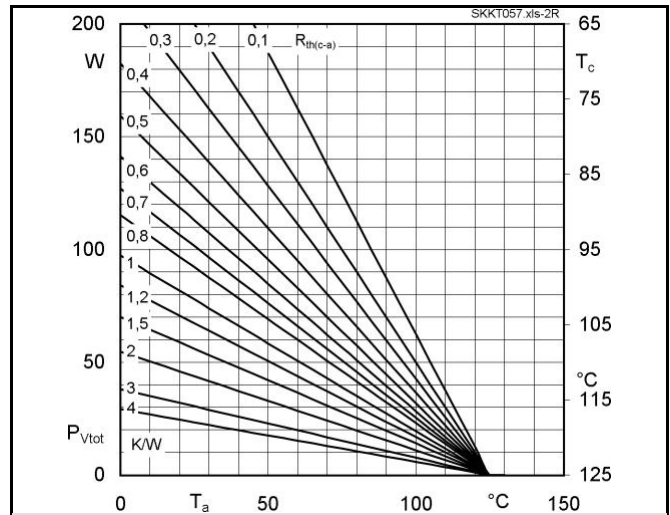


Fig. 2R Power dissipation per module vs. case temp.

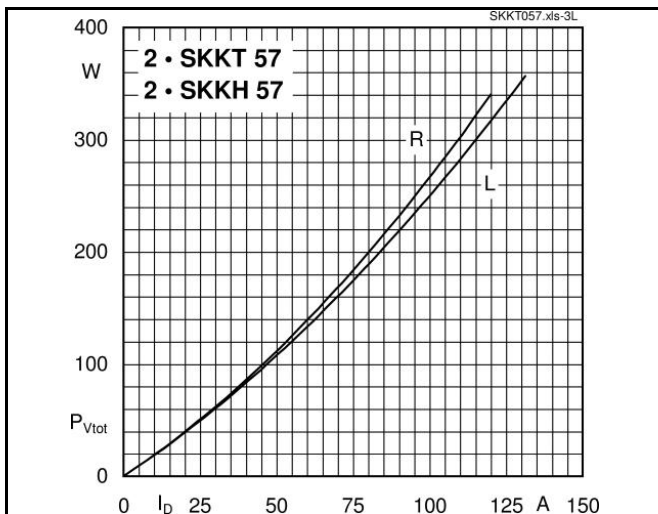


Fig. 3L Power dissipation of two modules vs. direct current

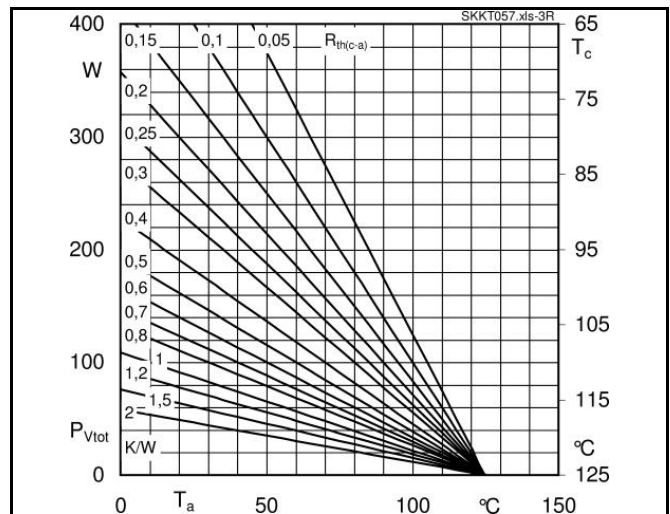


Fig. 3R Power dissipation of two modules vs. case temp.

# SKKT 57, SKKH 57, SKKT 57B

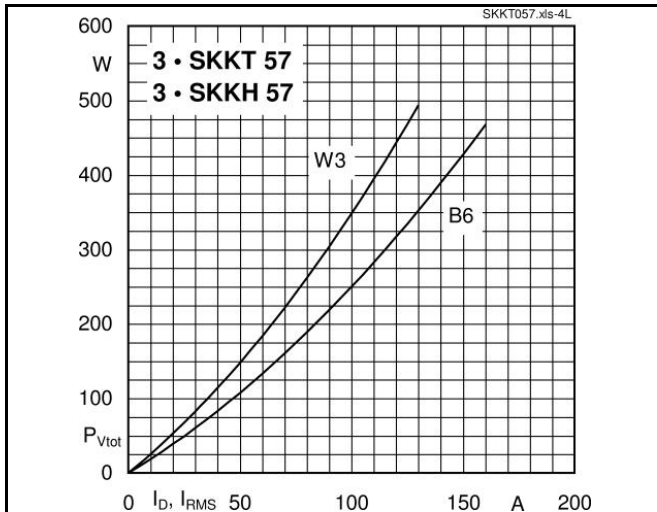


Fig. 4L Power dissipation of three modules vs. direct and rms current

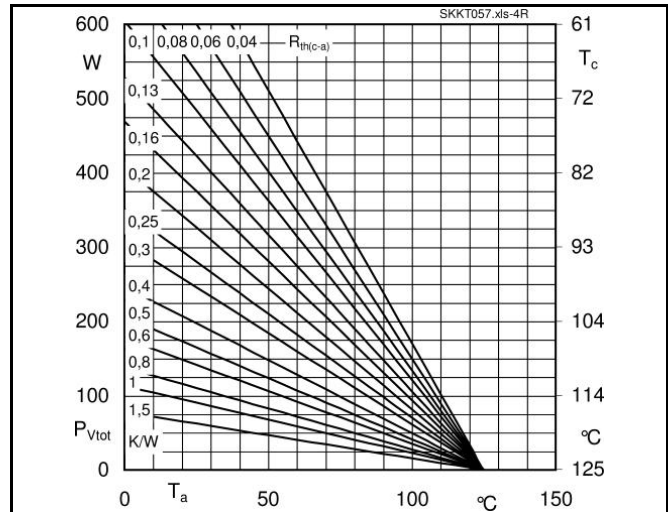


Fig. 4R Power dissipation of three modules vs. case temp.

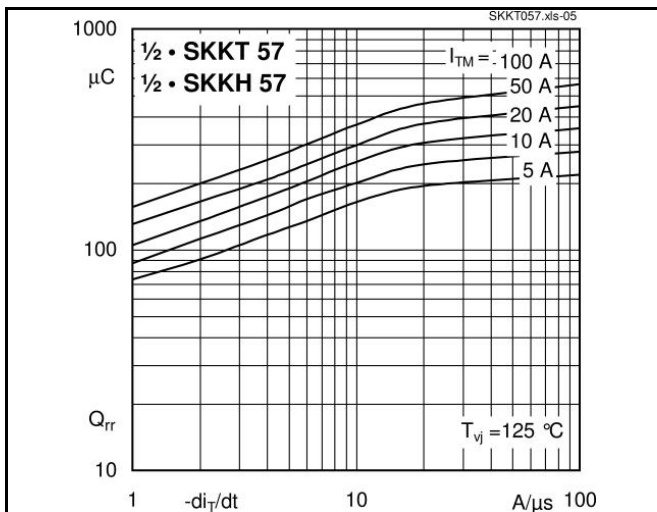


Fig. 5 Recovered charge vs. current decrease

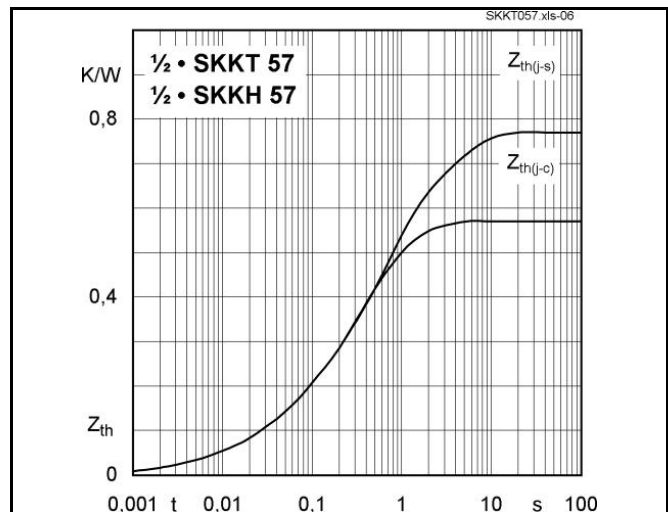


Fig. 6 Transient thermal impedance vs. time

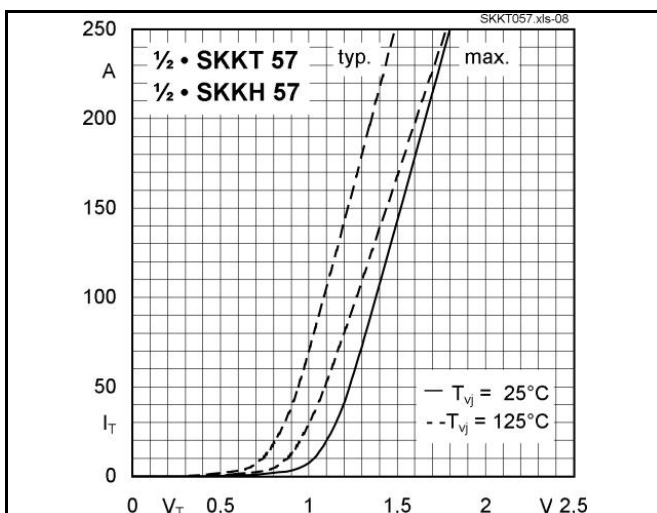


Fig. 7 On-state characteristics

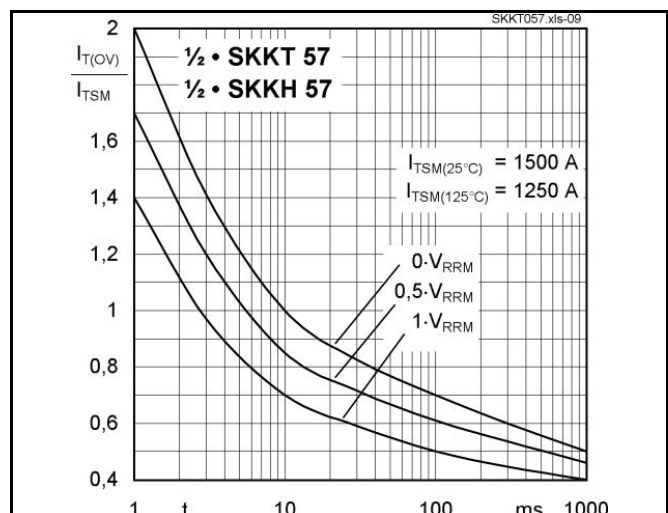
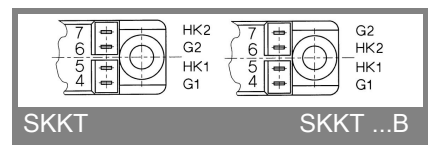
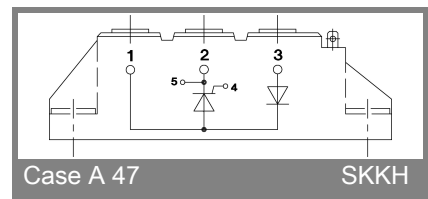
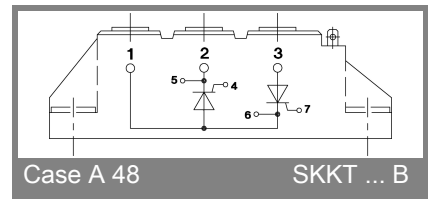
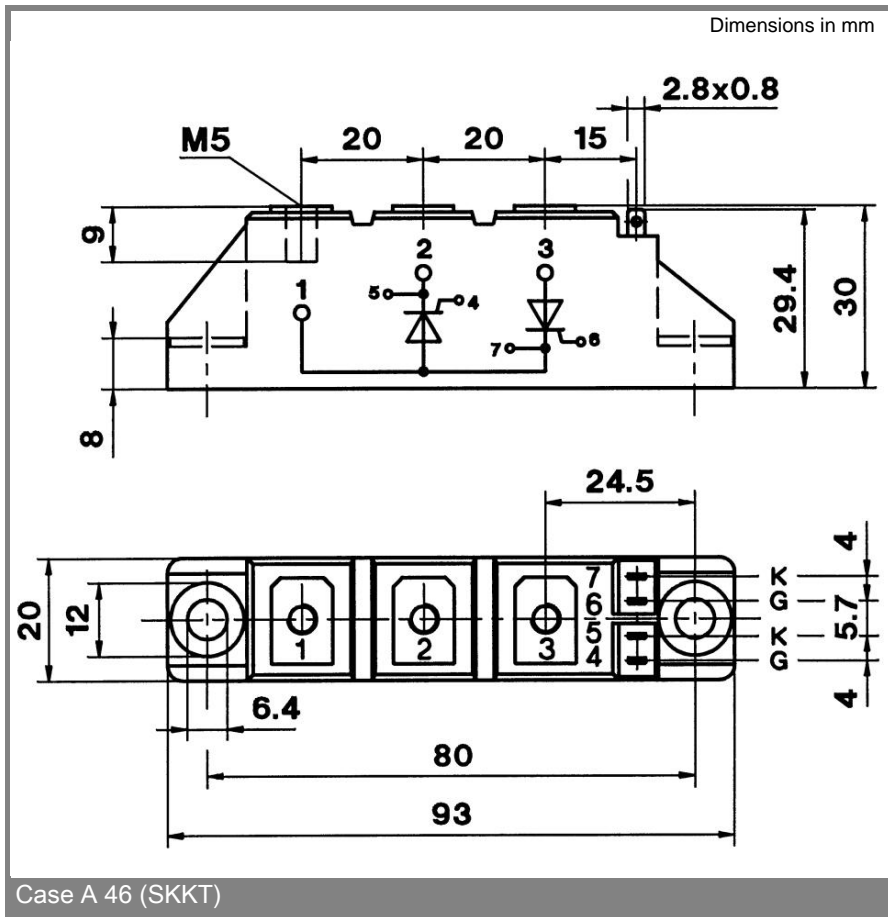
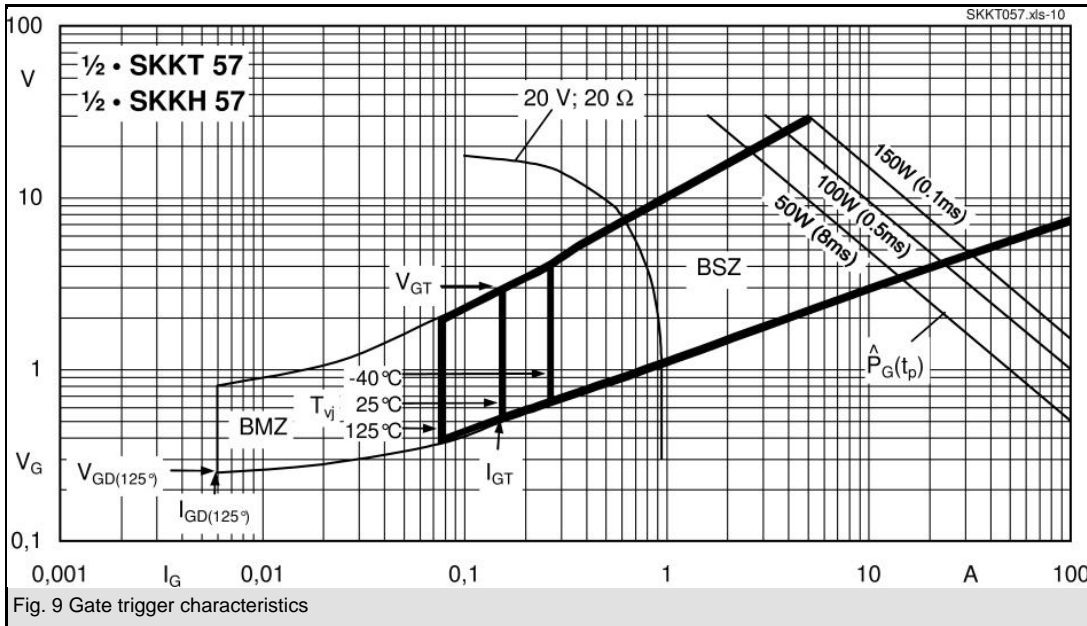


Fig. 8 Surge overload current vs. time



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